



**Future Missions to Titan:  
Scientific and Engineering Challenges**

**Low-Temperature Electronics:  
Opportunities for Titan Science**

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# A Reminder ...

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## Remember ...

**There is No Such Thing as Doing  
Interesting Science on Titan  
(Physics, Chemistry, Geology  
Biology, etc.) ...**



# Without a Robust Electronics Infrastructure!



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## A Personal Mandate:

**We Need to Get Rid of That  
Darn Warm Box!**



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**HOW?!**

# Low-T Operation



- **Pro's for Cooling Electronic Devices and Circuits:**

- mobility increases (depends on doping)
- current drive increases
- saturation velocity increases
- latchup in CMOS improves (BJT gain drops)
- thermally-activated failure mechanisms improve (e.g., electromigration)
- subthreshold swing and transconductance improve

- **Con's for Cooling Electronic Devices and Circuits:**

- carrier freeze-out can become an issue (depends on doping)
- breakdown voltages degrade
- hot carrier effects much stronger and can lead to major reliability issues
- heavy ion induced latchup in CMOS looks like a possibility (2010)
- TCAD simulation and compact modeling is a real challenge
- testing is painful
- cycling presents issues for electronic packaging

# Technology Options



## Assumptions:

- foundry supported (commercially available via MPW)
- low cost
- must support high levels of integration (e.g., mixed-signal SoC)
- can enable robust operation of complex electronics at 93K

## Technology Options / Comments:

### • Bulk Si CMOS

- most performance metrics improve with cooling
- cryo-T hot carrier lifetime is a serious issue to address
- best for digital; okay for analog/RF

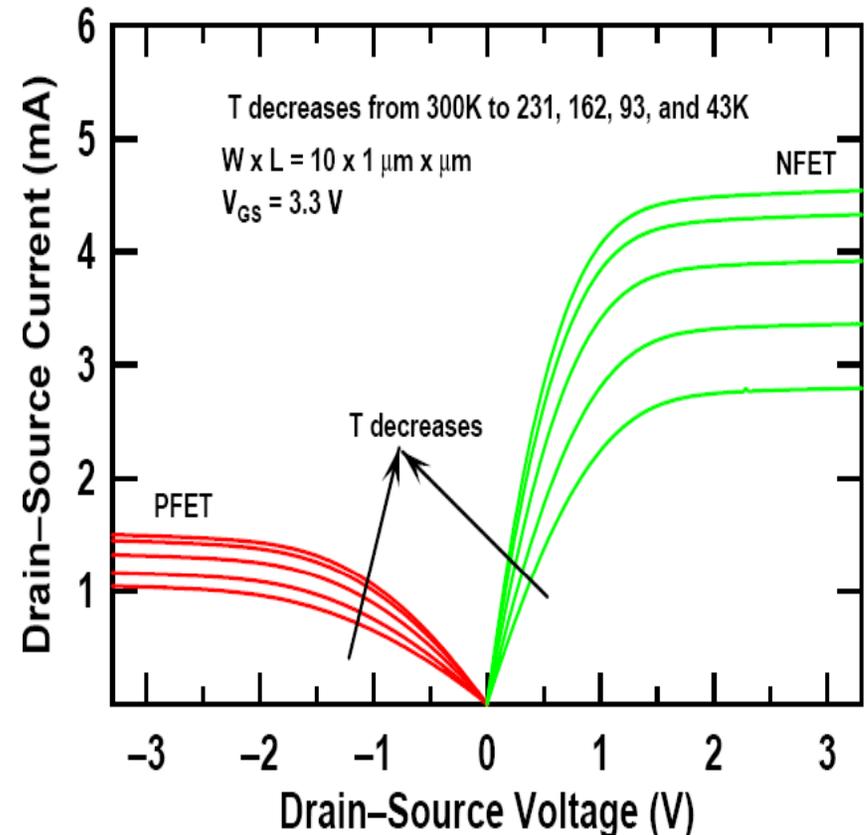
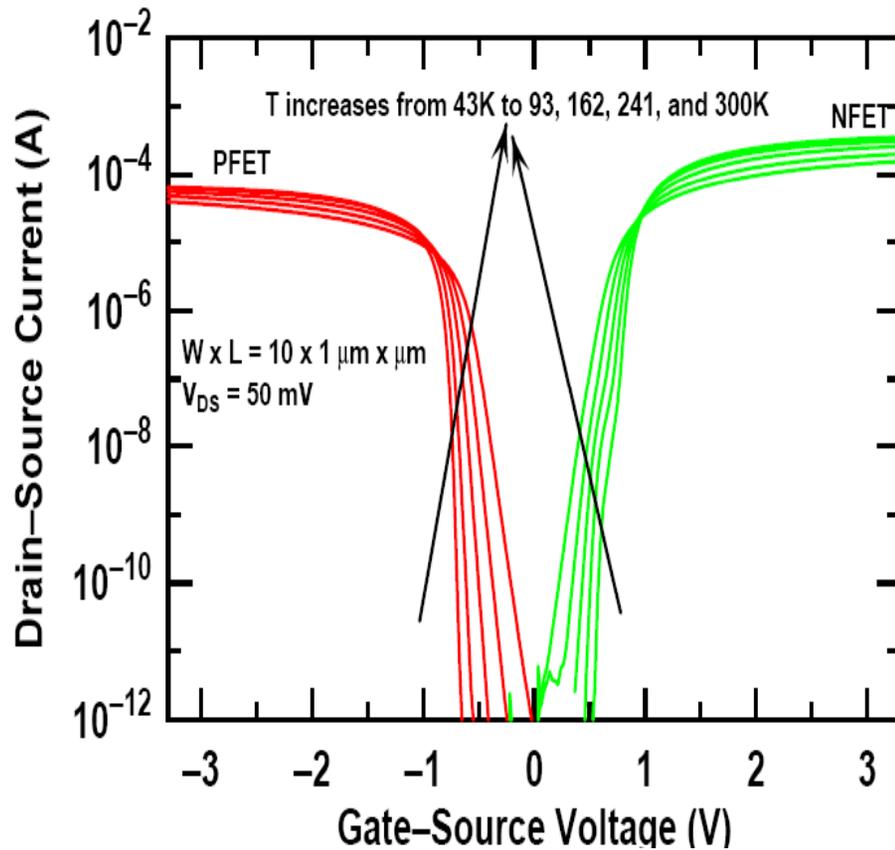
### • Bulk SiGe BiCMOS

- SiGe HBT performance improves with cooling (across board)
- no issue with SiGe HBT cryo-T reliability
- CMOS here has the same pro's/con's as for bulk CMOS
- BiCMOS gives optimal division of labor for analog/RF/digital

# Cryo-CMOS Performance



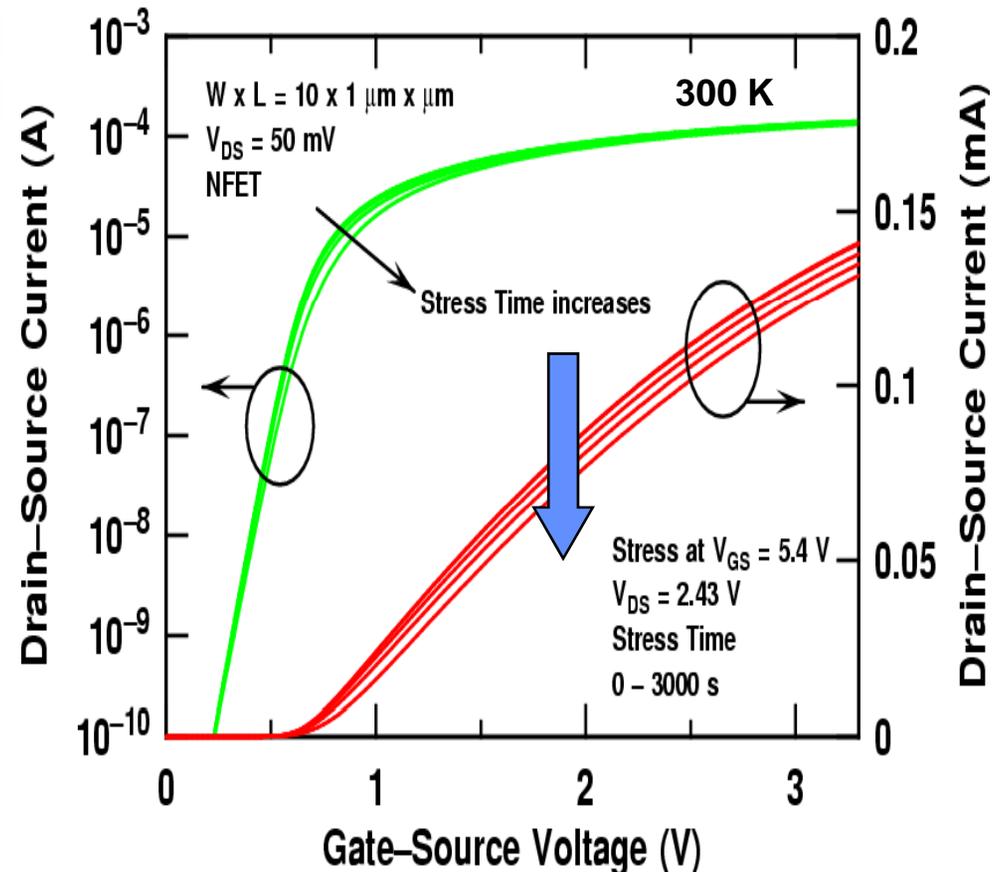
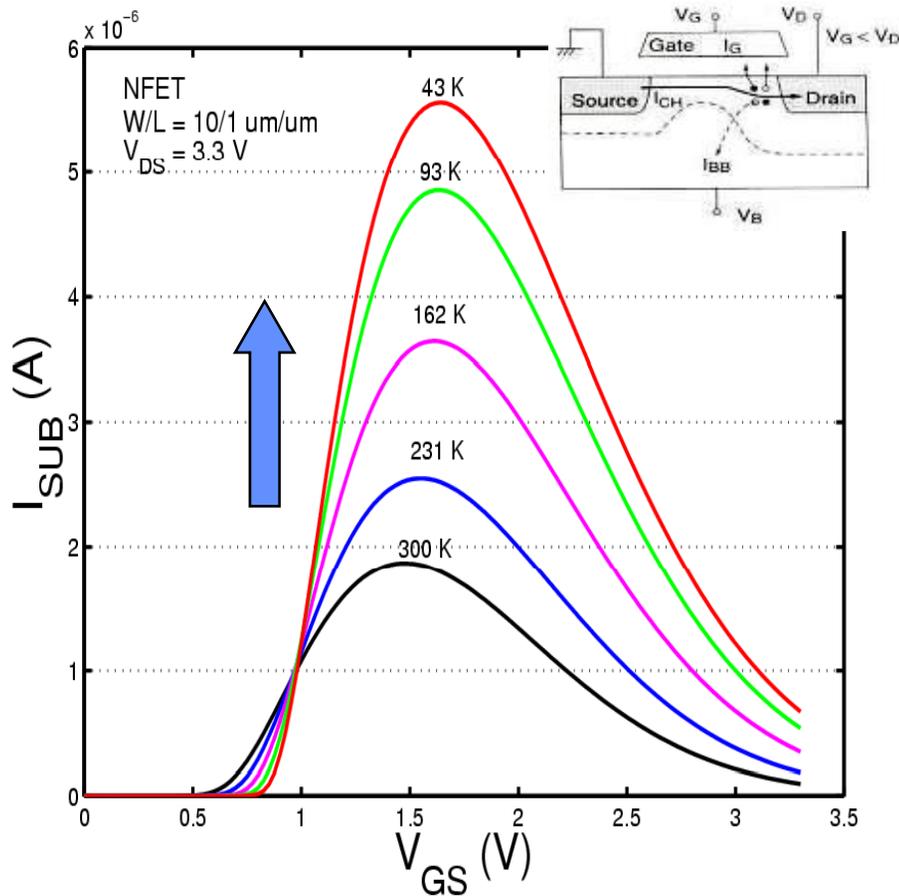
- CMOS Devices Function Well Down to 43 K
- Device Performance Improvement with Cooling ( $g_m$ ,  $\mu$ ,  $S$ )



# CMOS Reliability



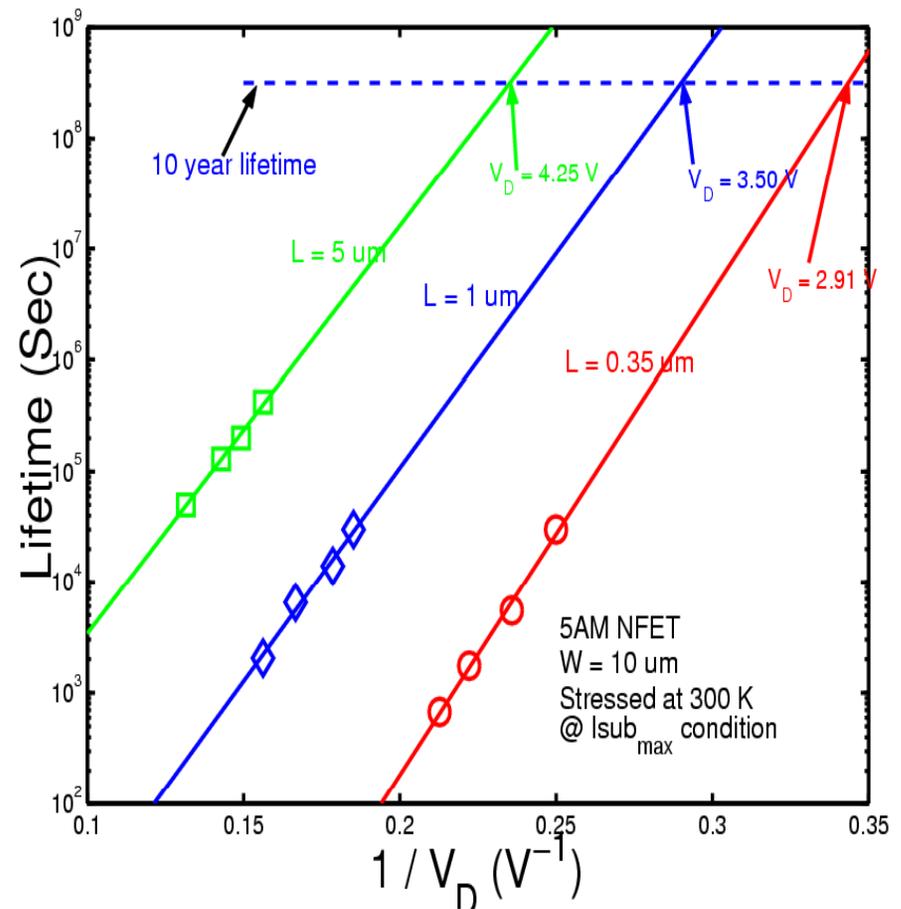
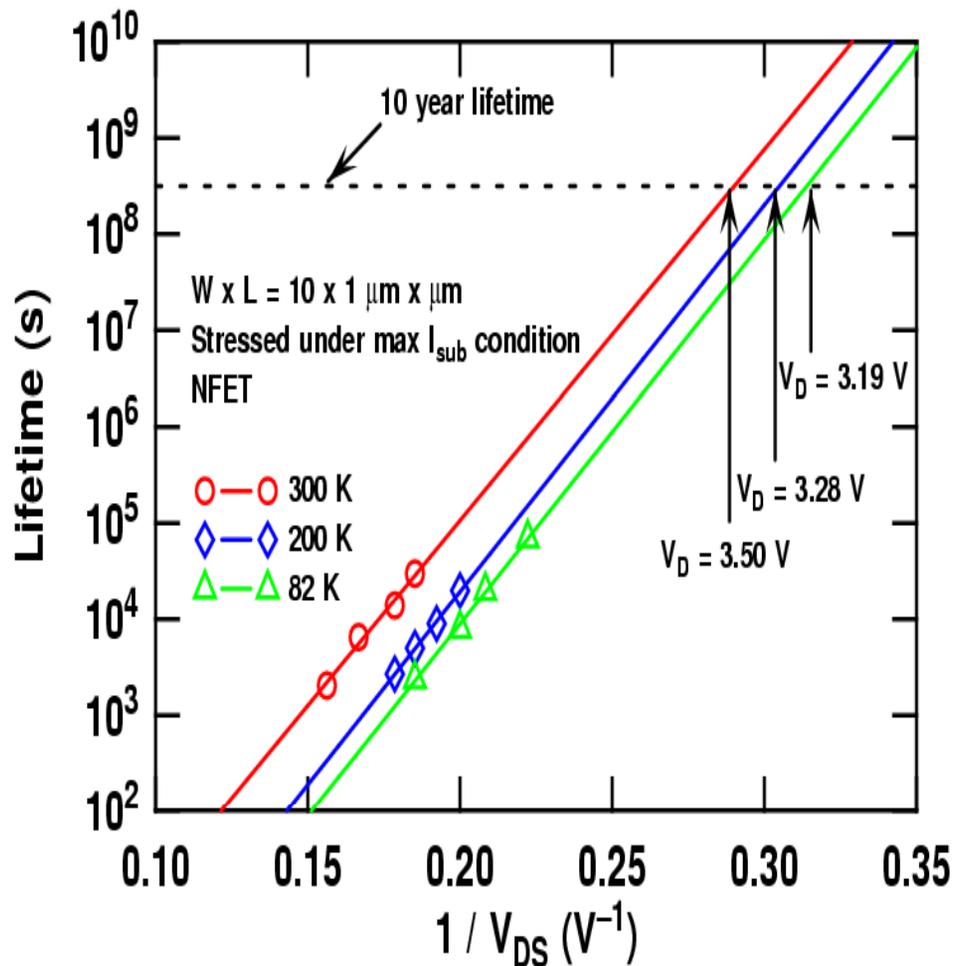
- $I_{SUB}$  is a Good Monitoring Parameter for HCE
- After Stress,  $I_d$  and  $g_m$  Decrease While  $V_T$  and  $S$  Increase



# L, T Dependence



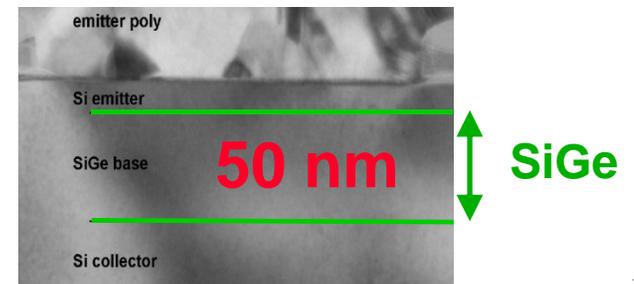
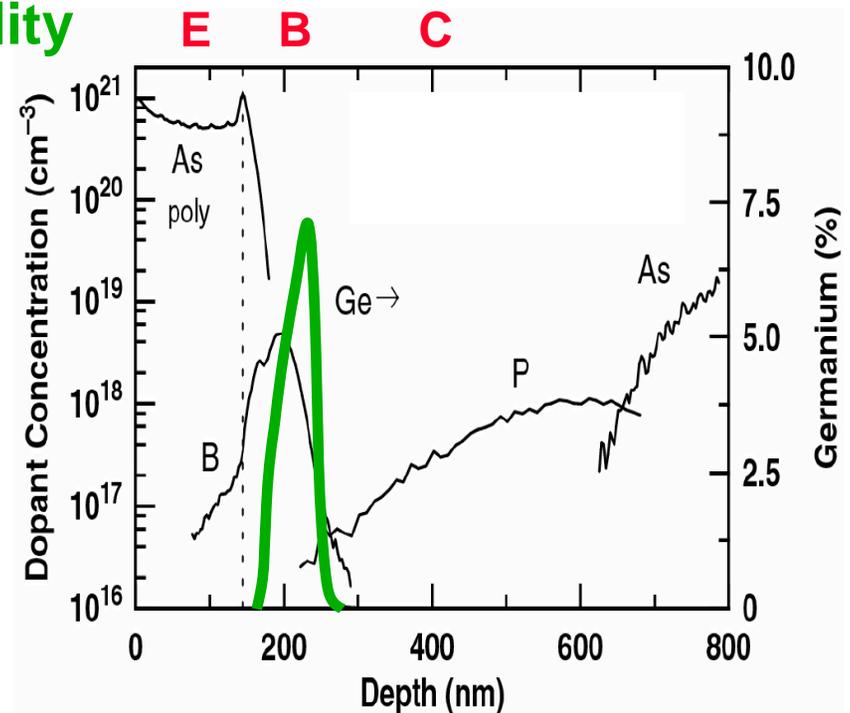
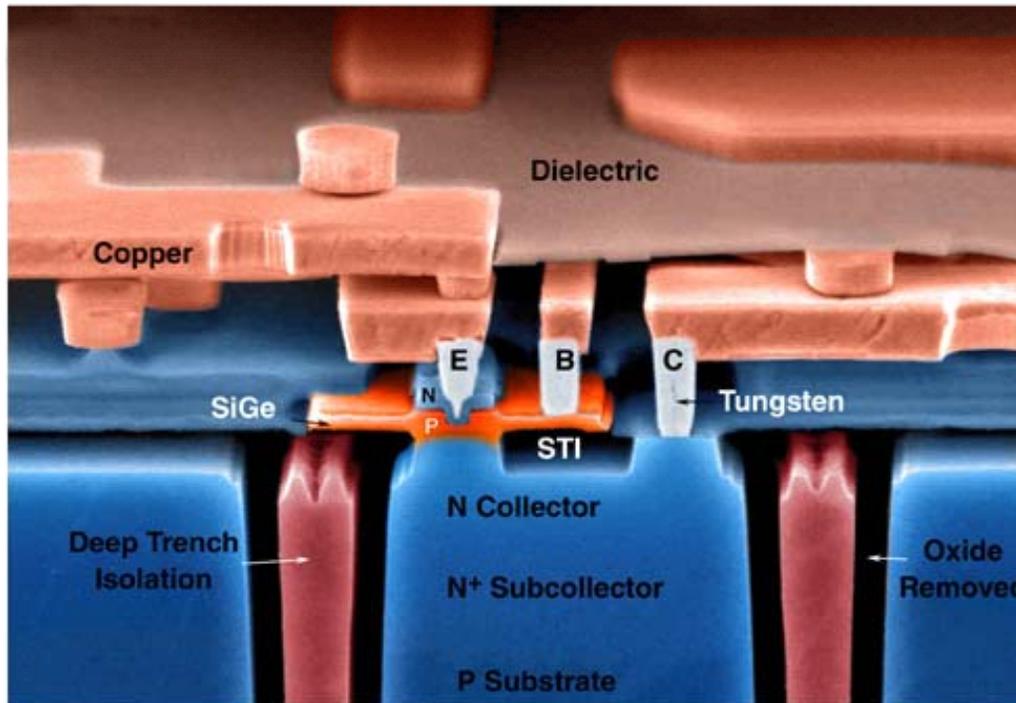
- Lifetime Decreases with Cooling at Fixed L
- Lifetime Decreases With L at Fixed T (Mitigation Path)



# The SiGe HBT



- Conventional Shallow and Deep Trench Isolation + CMOS BEOL
- Unconditionally Stable, SiGe Epitaxial Base Profile
- **100% Si Manufacturing Compatibility**
- SiGe HBT + Si CMOS on wafer

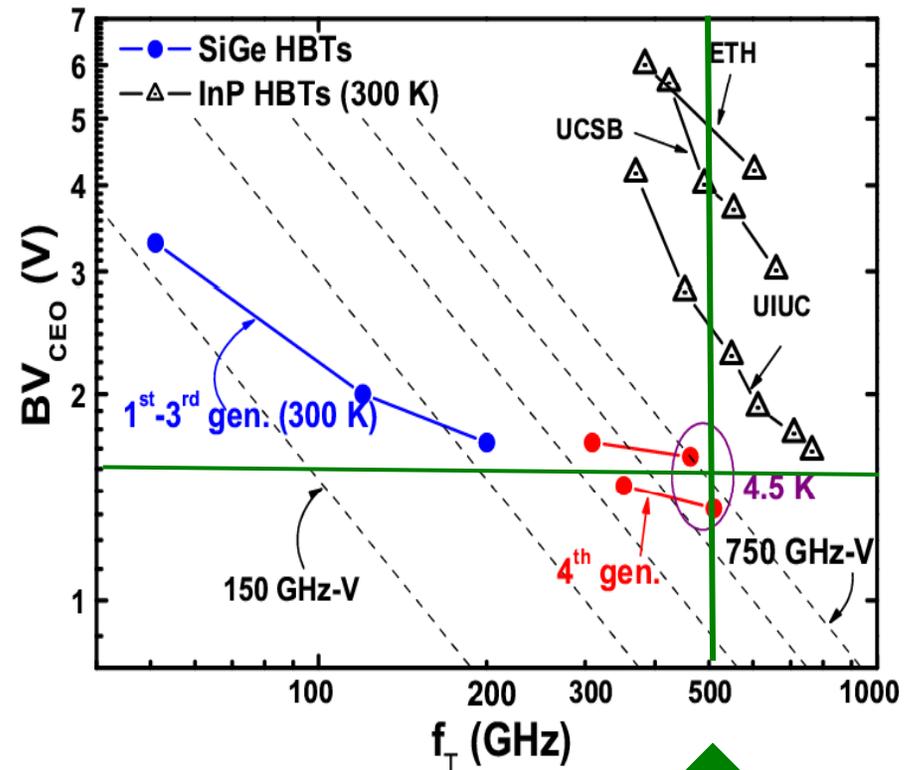
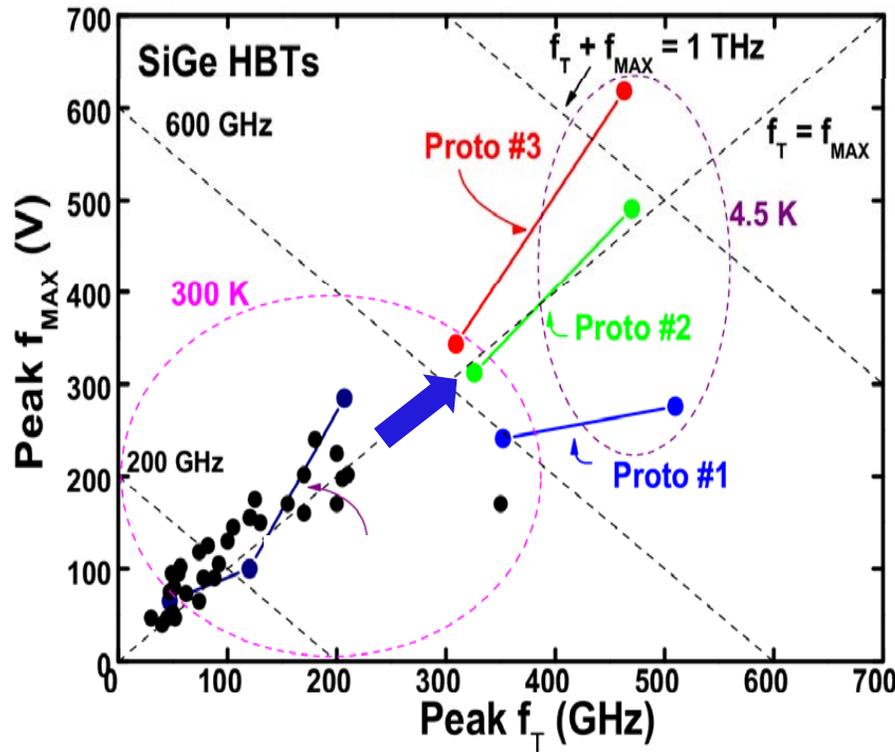


**SiGe = III-V Speed + Si Manufacturing Win-Win!**

# SiGe Performance Limits



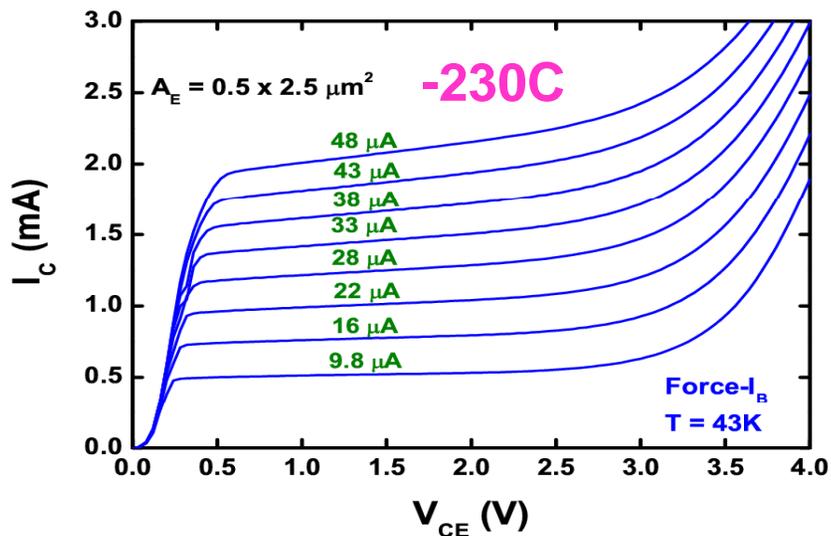
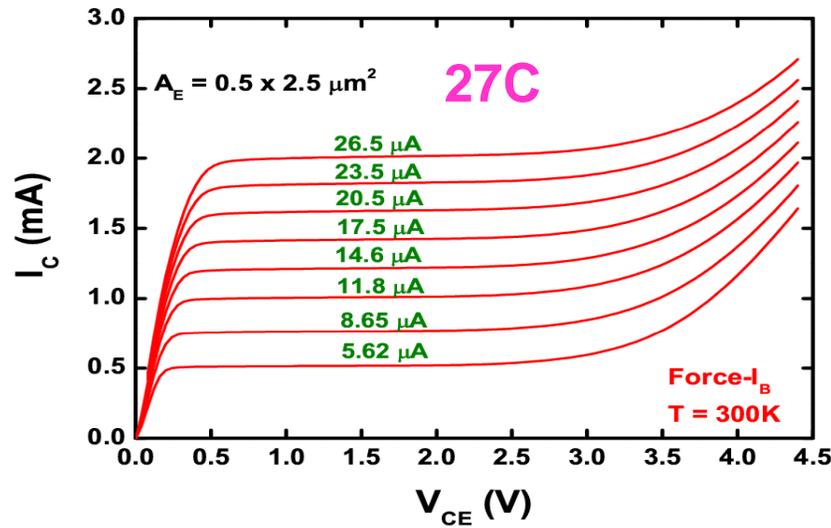
- Apparent Convergence of SiGe and III-V on Johnson Curve
- $f_T + f_{max} > 1$  THz in SiGe Is Clearly Possible (at very modest lith)
- Realistic Goal =  $BV_{CEO} > 1.5$  V @ 500 GHz  $f_T / f_{max}$



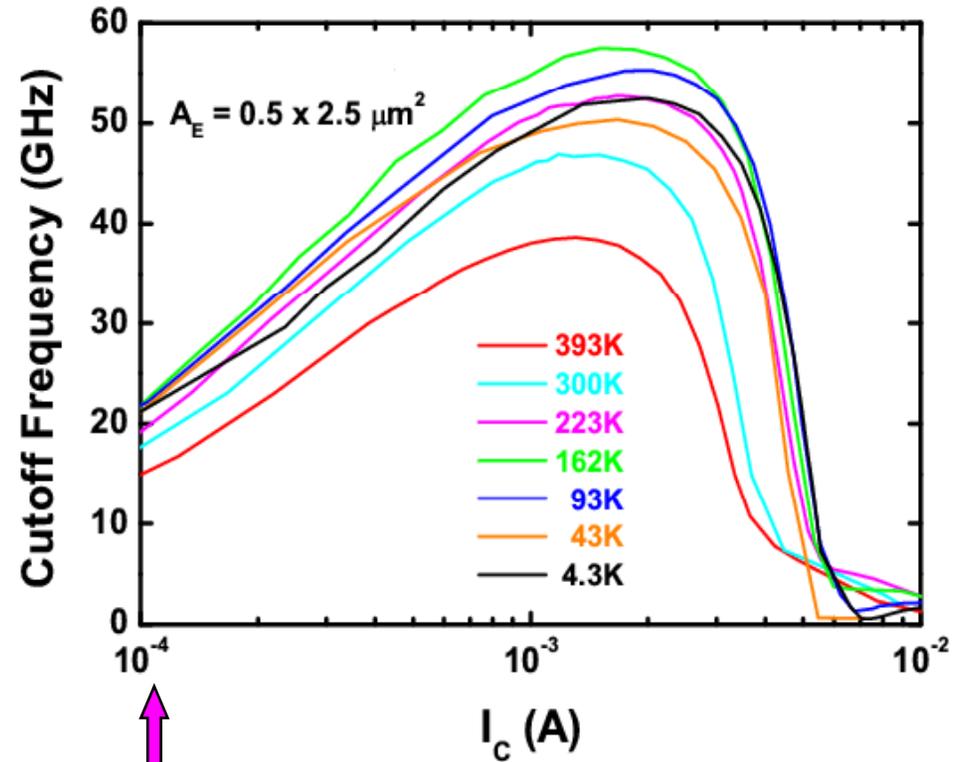
# SiGe HBTs at Cryo-T



dc



ac



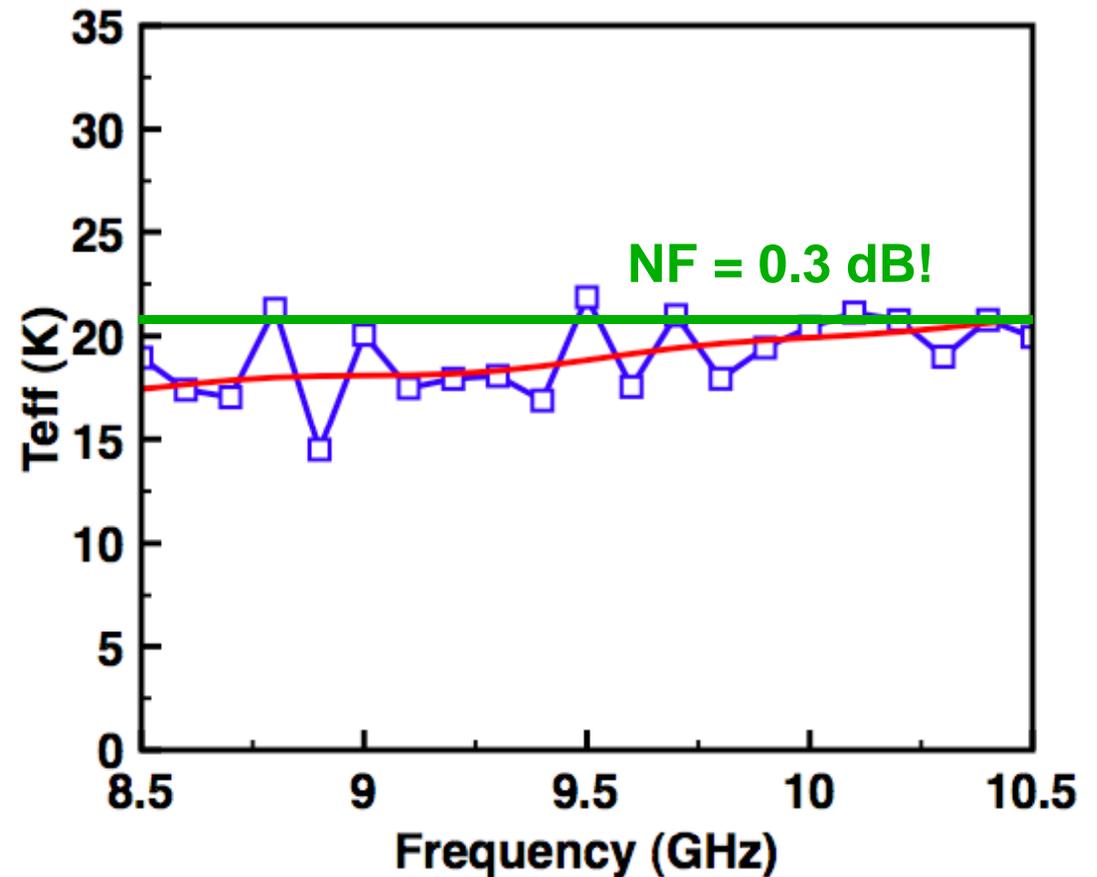
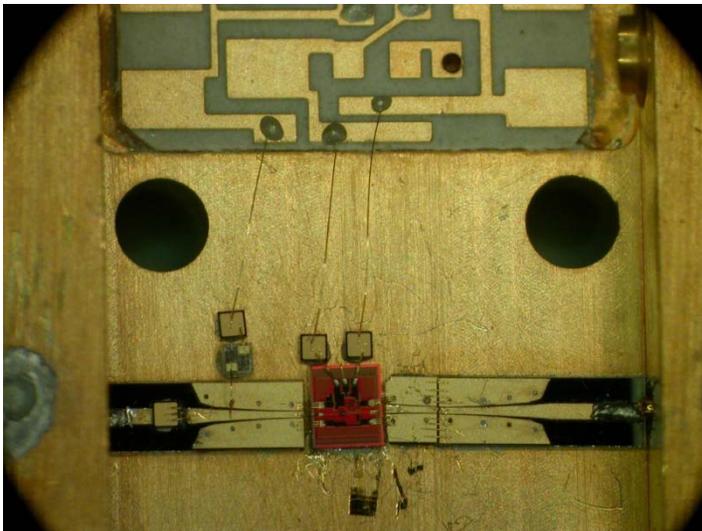
SiGe Exhibits Very High Speed at Very Low Power!

# Cryogenic SiGe LNAs



## X-band LNA Operation at 15 K (Not Yet Optimized!)

- $T_{\text{eff}} < 20$  K (noise T)
- **NF < 0.3 dB**
- **Gain > 20 dB**
- **dc power < 2 mW**



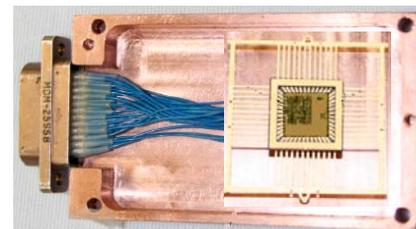
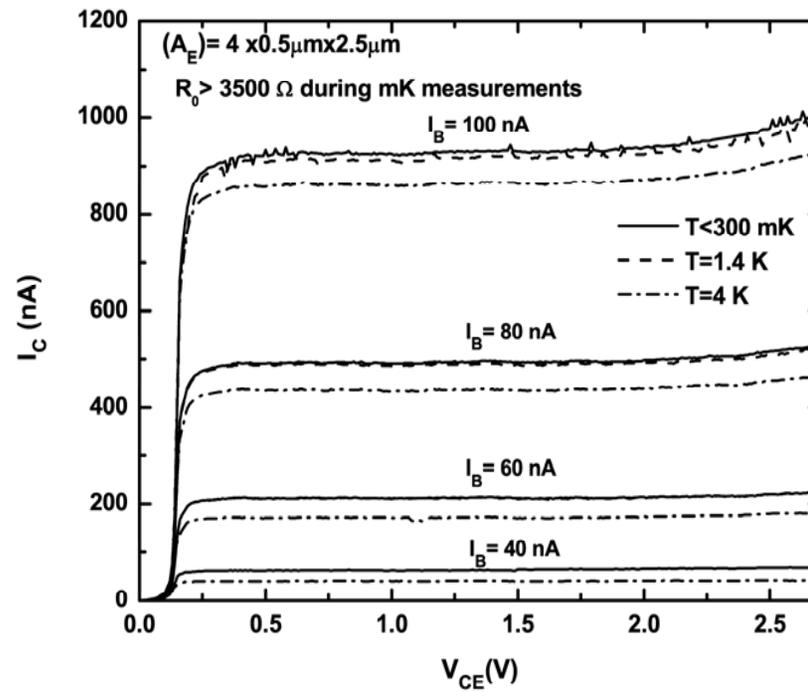
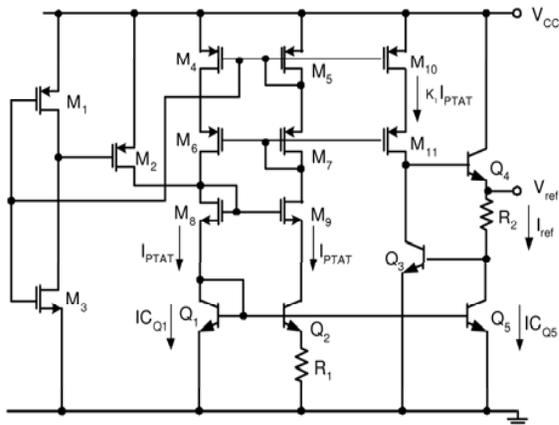
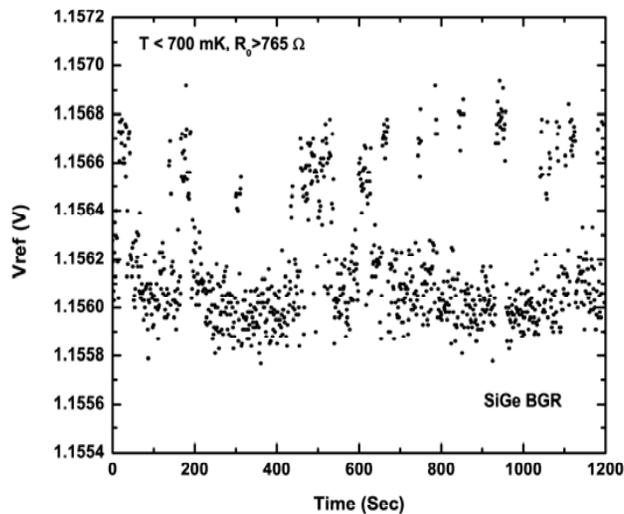
Collaboration with S. Weinreb, Cal Tech

**This SiGe LNA is Also Rad-Hard!**

# Operation at Sub-1K!



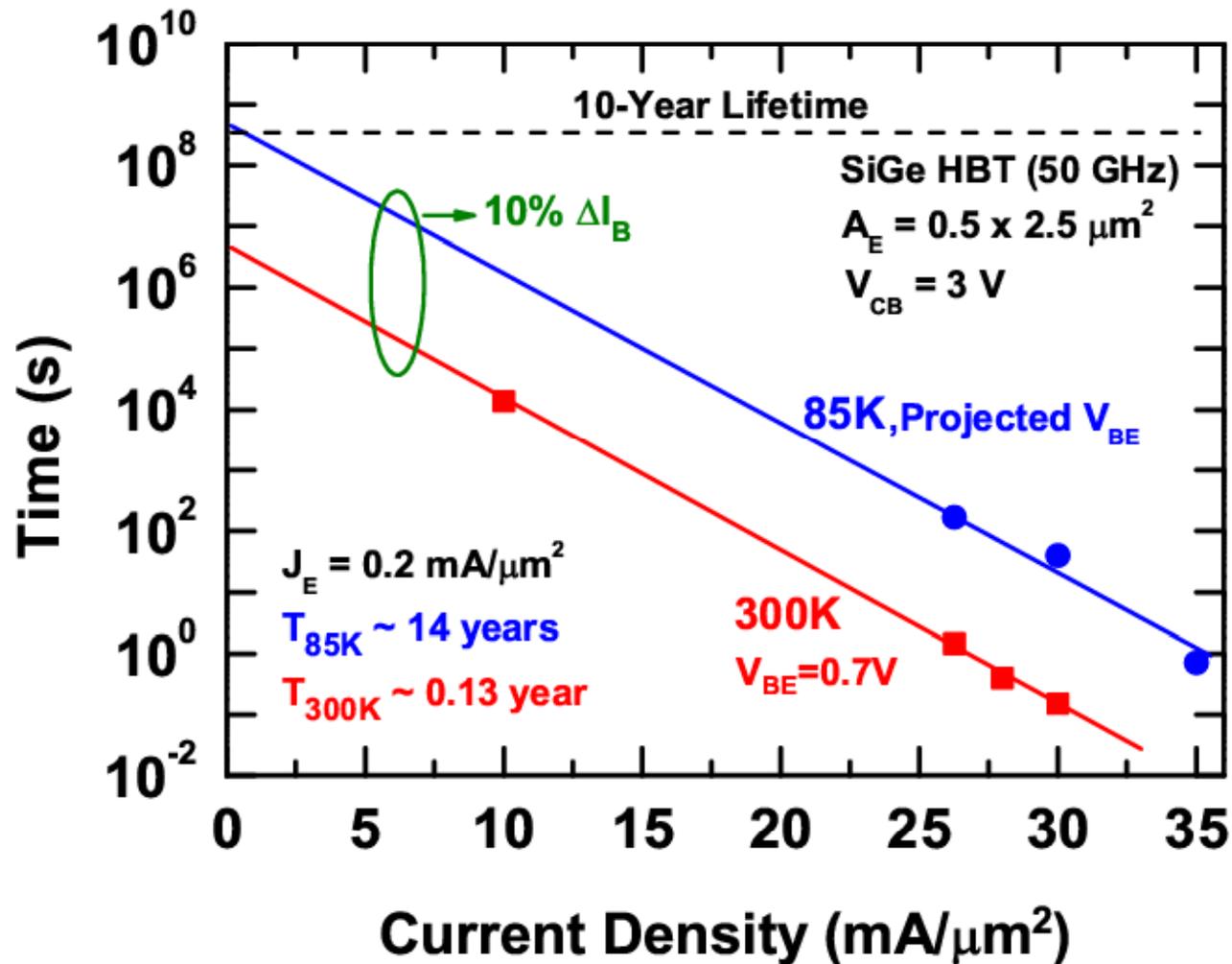
- SiGe HBT Works Just Fine Down to 300 mK!
- SiGe Bandgap Reference Circuit Also Works! (700 mK)



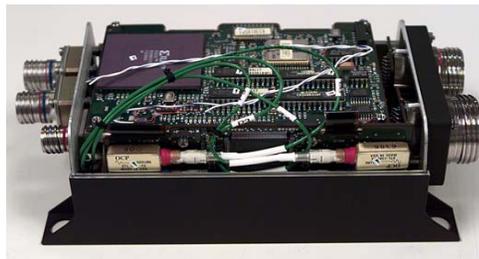
# SiGe HBT Reliability



- SiGe HBT Reliability Fine at Cryo-T



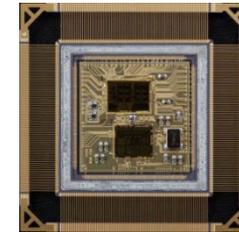
# Remote Electronics Unit



The X-33  
Remote Health  
Unit, BAE  
Systems,  
circa 1998



The ETDP SiGe Remote  
Electronics Unit, 2010

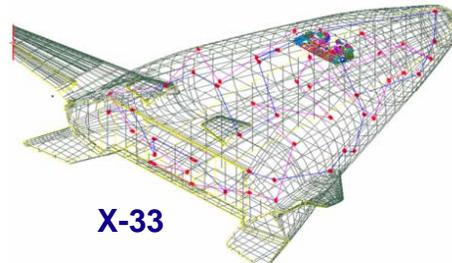
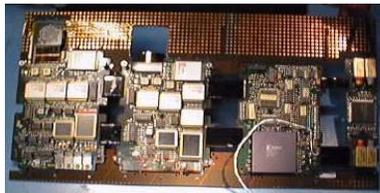
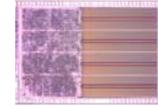


REU in a  
package!

SiGe Analog  
front end die



SiGe Digital  
control die



X-33

## Specifications

- 5" x 3" x 6.75" = 101 in<sup>3</sup>
- 11 kg
- 17 Watts
- -55°C to +125°C



## Our SWAP Goals

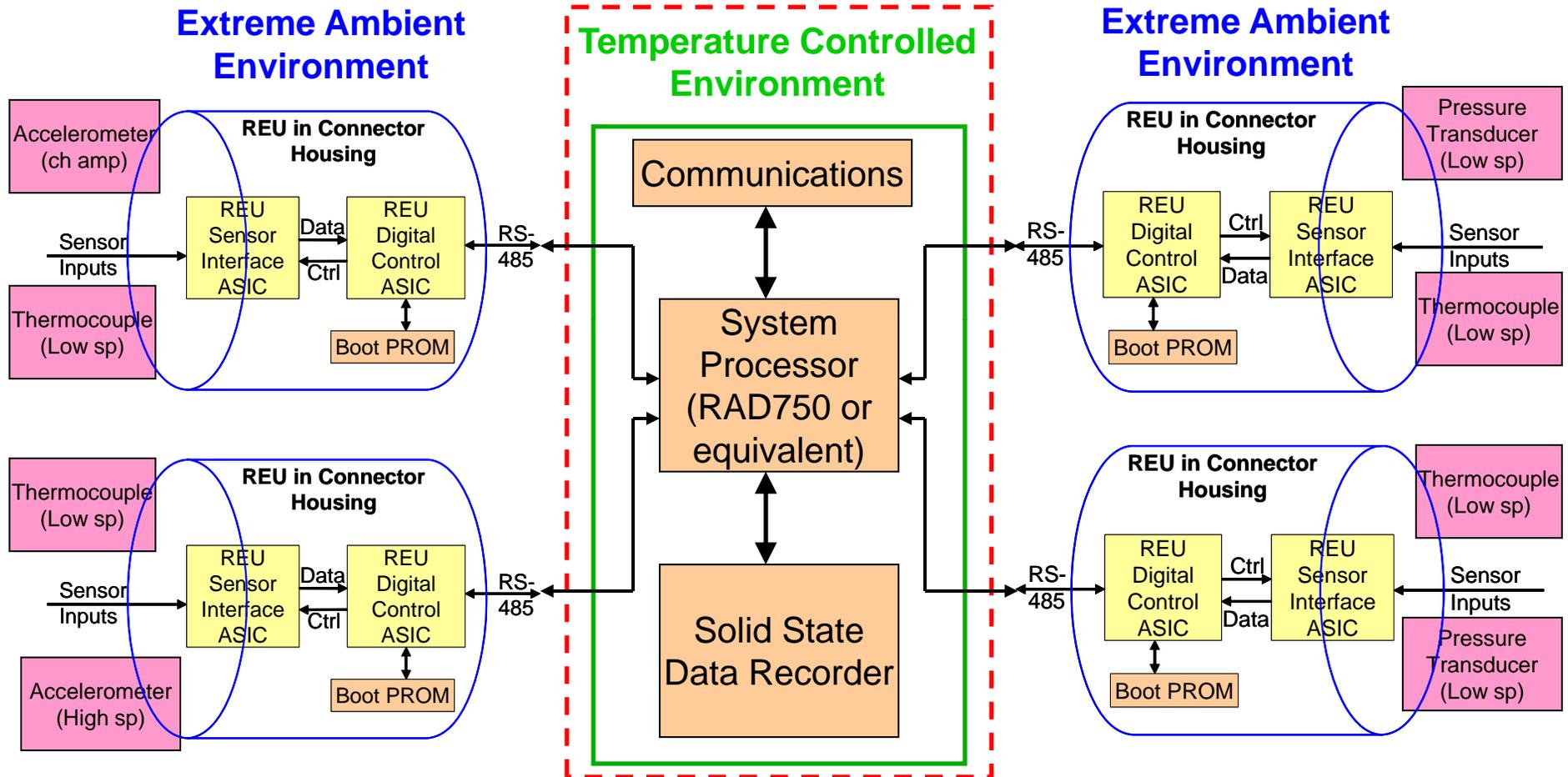
- 1.5" x 1.5" x 0.5" = 1.1 in<sup>3</sup> (100x)
- < 1 kg (10x)
- < 2 Watts (10x)
- -180°C to +125°C, rad tolerant

## Supports Many Sensor Types:

Temperature, Strain, Pressure, Acceleration, Vibration, Heat Flux, Position, etc.

Use This SiGe REU as a Remote Vehicle Health Monitoring Node

# SiGe REU Architecture



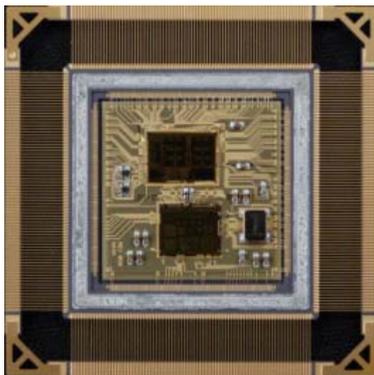
## Major Advantages:

- **Eliminates Warm Box** (size, weight, and power; allows de-centralized architecture)
- **Significant Wiring Reduction** (weight, reliability, simplifies testing & diagnostics)
- **Commonality** (easily adapted from one system to the next)

# Some Thoughts / Ideas



- We now know how to build robust, reliable, complex mixed-signal (analog, digital, RF) electronics to operate at Titan temperatures
- We can provide warm-box free “electronic suites” for a wide class of instrument / sensor / control / comm needs that can provide dramatic reductions in SWAP



**Complex On-Surface Electronics**  
analog, digital, RF, power, etc.

< 1.0 in<sup>2</sup>

< 100 g

< 1-2 W for electronics SYSTEMS

**Read:** [Environmental Invariance](#) (e.g., 90 K)

# Some Thoughts / Ideas



- **Old Idea:** one big, heavy, power hungry science package with lots of instruments drops to the surface
- **New Idea:** identify a “few” (or lots!) target science sensor/instruments (e.g., lab on a chip) that can be packaged at small size and low power and then deploy a “platoon” of such small environmentally invariant science packages by parachute to the surface (land and lake - boat with a sail?), each of which have low-power RF links (operating at ambient) for comm from package-to-package or package-to-balloon or package-to-orbiter
- Design small science packages to run off batteries for “long” duration operation, and perhaps even enabled to scavenge energy if desperate (beam RF from orbiter?)